

## Features of Anomalous Small of Strain Coefficient

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The analysis of one of the neglected problem of strain effect – causes observation anomalous small longitudinal strain coefficient ( $\gamma_l$ ). It is concluded that the value of  $\gamma_l < 3$  units will take place in the case where in the quasi elastic or plastic deformation Poisson coefficient is more than 0.5. Discussed possible reasons for this increase.

**Keywords:** Strain effect, Poisson coefficient, Gruneisen constant, Debay temperature, Anomalous small strain coefficient.

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### 1. INTRODUCTION

In works by G.Kuczynski [1], R.Parker and A.Krinsky [2], Z.Meiksin and Hudzinski [3] have laid the theoretical and experimental investigate of the strain effect in the metal wires and thin films. For today investigated almost all aspects of this effect. In particular, by taking into account the contribution of surface and grain-boundary electron scattering [4] in the coefficient of and transverse strain for one-layer films. We proposed a phenomenological model [5] for the longitudinal strain coefficient, which takes into account the dependence of strain not only mean free path of electrons ( $\lambda_0$ ) in the bulk of crystal grains, but the parameter of specular reflection from external surface film, transmission coefficients of grain boundaries and interfaces in the multilayer film systems. Testing of this model has given satisfactorily results. Along with the studies of external and internal classical size effects in strain effect for one-layer films and multilayers has gained significant experimental material about film alloys Ni-Cr [6, 7], Ni-Co [8], Ni-Fe [9, 10], heterogeneous [11, 12] and diamond and diamond like [13-16] materials.

Along with research of the strain effects focuses on mechanical properties and plastic deformation mechanisms of the free films and films on the substrate. It has been clearly established that the mechanical properties (Young's modulus, strength, strain at which the transition to plasticity) fine-dispersed films and bulk materials are quite different. In the case of coarse-dispersed films mechanical properties, with the exception of plasticity, does not differ significantly.

Systematic study of size effect in plasticity of films Cu, Al and Au (thickness from 0.2 to 1  $\mu\text{m}$ ) and multilayers of Cu/Ni presented in works [17-19]. These studies are important for the correct interpretation of the results for strain effect, because the value  $\gamma_l$ , it is completely determined by the type of deformation – elastic, quasi elastic or plastic. According to different authors deformation transition from elastic to plastic

deformation ( $\varepsilon_{lr}$ ) for films has a values: 0.10-0.20 (Cr); 0.25-0.52 (Pd); 0.30-0.40 (Fe / Cr); 0.25 (Cu / Cr) and 0.48 % (Pd / Fe).

Analyzing a many results for strain effect, we conclude that at present remains unclear cause of thin films anomalous small values  $\gamma_l$  under which we mean all values  $\gamma_l$  less than a certain limit value strain coefficient  $\gamma_l^b$ , which corresponds to the Poisson coefficient of film  $\mu_f = 0.5$ . Definitely estimate the value  $\gamma_l^b$  impossible, but approximate its value within  $\gamma_l^b \cong (1 + 2\mu_f) \div 3$  units.

Because preliminary research results of strain effect in films Pd, Ag and others and the results of work [21] for films Pt indicate anomalous small value ( $\gamma_l$ ), than the aim of this work was to detailed study of strain effect in Pd and Pt films and analyzing the future of anomalous strain coefficient.

### 2. TECHNIQUE OF EXPERIMENT

Thin Pd and Pt films were obtained by thermoresistive evaporation in a vacuum  $\sim 10^{-4}$  Pa at substrate temperature  $T_s = 300$  K.

Tensoresistive properties were investigated for five-seven deformation cycles "loading-unloading" at strains intervals  $\Delta\varepsilon_{l1} = (0-1)$  % and  $\Delta\varepsilon_{l2} = (0-2)$  % by standard method.

Average strain coefficient ( $\gamma_l$ ) and momentary strain coefficient ( $\gamma_{lm}$ ) defined by the ratio  $\gamma_l = \frac{1}{R_0} \frac{\Delta R}{\Delta\varepsilon_l}$

and  $\gamma_{lm} = \frac{1}{R_i} \frac{dR_i}{d\varepsilon_{li}}$ , respectively, where  $R_0$  – initial electrical resistance in the longitudinal deformation,  $R_i$  and  $dR_i$  – film resistance at the beginning of the interval  $d\varepsilon_{li}$  and its change with increasing longitudinal strain on  $d\varepsilon_{li}$ . Value  $\gamma_l$  was calculated as the slope of dependence

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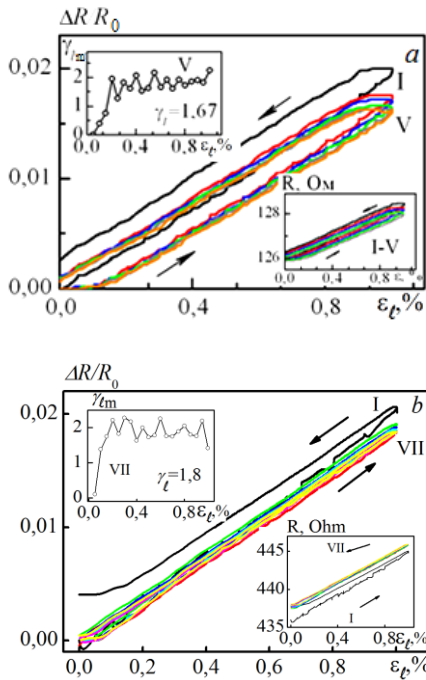
$\Delta R/R_0$  versus  $\varepsilon_l$ , and averaging in the interval  $\Delta\varepsilon_l$  value  $\gamma_{lm}$  which is calculated based graphical derivation of dependence  $d \ln R_i$  by  $\varepsilon_l$ . Both procedures give the same value  $\gamma_l$ . Measurement technique  $\gamma_l$  and  $\gamma_{lm}$  is set out in more detail in article [21].

Electronographic and structural studies were carried out using a device with a high a resolution ПЕМ-125К (firm "SELMI").

### 3. RESULTS AND DISCUSSION

Pd and Pt films after condensation have nanocrystalline structure and the fcc-lattice with a lattice parameter nearest to the value for the bulk samples. Fig. 1 illustrates a typical deformation dependence  $R$  i  $\Delta R/R_0$  versus  $\varepsilon_l$  for the interval deformation (0-1) %.

From these results it follows that the value  $\gamma_l$  depends on the type of strain cycle and from V-VII cycles saturates. Note that the thin film Pd and Pt, as well as other noble metals, are characterized by relatively wide intervals plastic or quasi-elastic deformation. This is evidenced by the linear nature of the dependence  $R$  and  $\Delta R/R_0$  versus  $\varepsilon_l$  for II-VII cycles (Fig. 1). On Fig. 2 shows the size dependence of the average strain coefficient for the Pd and Pt films.

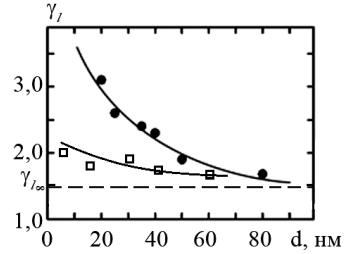


**Fig. 1** – Strain dependence  $R$  and  $\Delta R/R_0$  versus  $\varepsilon_l$  for Pd (a) and Pt (b) films. The inset – strain dependence of the momentary strain coefficient and  $R$  versus  $\varepsilon_l$

Classical theory of strain effect in bulk samples developed in article [1] and in the most general form longitudinal strain coefficient is written as:

$$\gamma_l \equiv \frac{d \ln R}{d \varepsilon_l} = \frac{d \ln \rho}{d \varepsilon_l} + (1 + \mu_f + \mu'_f) \cong \frac{d \ln \rho}{d \varepsilon_l} + (1 + 2\mu_f), \quad (1)$$

where  $R$  and  $\rho$  – resistance and resistivity;  $d\varepsilon_l = d \ln l$  – longitudinal deformation ( $l$  – length of sample) and  $\mu'_f = \mu_f \cdot \frac{1 - \mu_s}{1 - \mu_f} \cong \mu_f (\mu_s - \text{Poisson coefficient of substrate})$ .



**Fig. 2** – Size dependence of the average strain coefficient for Pd (□) and Pt (●) films

The first term  $\gamma_l^p$  is associated with internal electronic properties of the material, and the second term – a so-called geometric factor that is associated with the change of geometrical dimensions of the sample. Assuming that  $\rho \approx n^{-1} \lambda_0^{-1}$  ( $n$  – effective concentration of free electrons), the author [1] received the ratio  $\gamma_l^p$ :

$$\gamma_l^p = \frac{d \ln \rho}{d \varepsilon_l} = - \left( \frac{\ln \lambda_0}{d \varepsilon_l} + \frac{d \ln n}{d \varepsilon_l} \right) = \frac{2 d \ln \Theta_D}{d \varepsilon_l} + 1, \quad (2)$$

where  $\Theta_D$  – Debye temperature at the film.

Considering that the  $\frac{d \ln \Theta_D}{d \ln V} = \gamma$  ( $V$  – volume,  $\gamma$  – Gruneisen constant), ratio (2) can be rewritten as:

$$\gamma_l^p = 1 + 2\gamma(1 - 2\mu_f) = 1 + \eta_{\lambda_0 l}, \quad (2')$$

and ratio (1) converted to the form:

$$\gamma_l = 1 + (2\gamma - 4\mu_f\gamma) + (1 + 2\mu_f), \quad (3)$$

where  $\eta_{\lambda_0 l} = - \frac{d \ln \lambda_0}{d \varepsilon}$  – strain coefficient of  $\lambda_0$ .

From ratio (3) it follows that  $\gamma_l^b = \lim \gamma_l = 2(1 + 2\mu_f) \approx 3$  (although the condition  $\gamma_l^p = 0$  value is  $\gamma_l^b = 2$ ). The authors [23] have analyzed this issue for thin films in the framework of the Fuch-Sondgeimer (FS) in the limiting case of small thicknesses ( $\frac{d}{\lambda_0} \cong 1$ ,  $d$  – film thickness). They got value

for  $\gamma_l$  provided at the condition  $\rho \cong \lambda_0^{-1} n^{-\frac{3}{2}}$ :

$$\gamma_l = 2 \left( \frac{5}{6} + \mu_f \right) + (2\gamma - 4\mu_f), \quad (4)$$

that the  $\mu_f = 0.5$  gives the value  $\gamma_l^b = 2.7$ .

Our analysis shows that the cause of anomalously small values  $\gamma_l$  of the gauge can be explained within

the framework of the ratio (3) or (4). Calculate the value  $\mu_f$  for different values  $\gamma_l$  at the fixed values of Gruneisen constant (Fig. 1) indicate that anomaly small size  $\gamma_l$  occur at a value  $\mu_f > 0.4$ , i.e. in the quasi- and plastic deformation. Despite the fact that the strain  $\varepsilon_{tr}$  was measured with sufficient accuracy based on strain diagram, it cannot be established on the basis of the size dependence  $\gamma_l$  from  $d$ , and since  $\varepsilon_{tr}$  size dependent value.

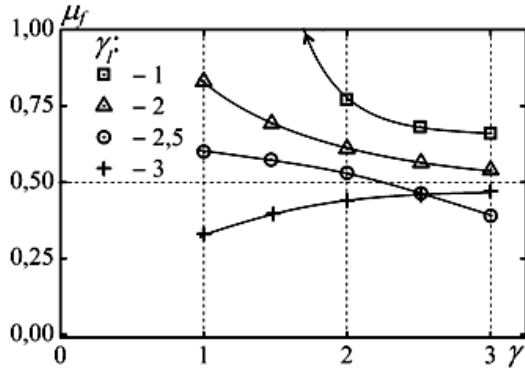


Fig. 3 – Calculated values  $\mu_f$  based on equation (4) for different values  $\gamma$  and  $\gamma_l$ . From article [24]

This may have this could lead to the fact that the size dependence  $\gamma_l$  versus  $d$  [2, 9, 10, 16, 21] were obtained in the elastic deformation (relatively small thickness) or quasi elastic and/or plastic deformation (thick films).

From the relations (3)-(5), it follows that the value  $\gamma_l$  is completely determined terms  $(2\gamma - 4\mu_f\gamma)$ : at  $\mu_f < 0,5$  it gives positive contribution to the value  $\gamma_l$ , while for large  $\mu_f$  (more than 0,5) – from capacious contribution. From Fig. 1 shows that when  $\gamma_l < 2.5-3.0$  units, then  $\mu_f$  has a value greater than 0.5, i.e. the deformation of the film takes place in the area of quasy elasticity or plasticity. The curves for  $\gamma_l = 1; 2$  and 2.5 indicates that explain the reason for anomalously small values  $\gamma_l$  just based on the idea increasing  $\mu_f$ , not because you have to allow for an increase in  $\mu_f$  to a value greater than  $\gamma_l = 1$ . Thus, in this case, the in-

creased  $\mu_f$  must increase was Gruneisen constant.

Really, when you consider that the minimum wavelength phonons  $\lambda_{\min} = 2a$  ( $a$  – lattice parameter), then change  $\Theta_D$  for the strain longitudinal phonon spectrum mode decrease the equation:

$$\Delta\Theta_D^x = \frac{hv_{ph}}{2k_B} \cdot \left( \frac{1}{a \cdot (1 + \mu_f \varepsilon_l)} - \frac{1}{a} \right) = \frac{v_{ph}}{2k_B a} \cdot \left( \frac{\mu_f \varepsilon_l}{1 + \mu_f \varepsilon_l} \right)$$

and slightly increased in the case of transverse oscillation modes:

$$\Delta\Theta_D^{y,z} = \frac{hv_{ph}}{2k_B a} \cdot \left( \frac{\mu_f \varepsilon_l}{1 - \mu_f \varepsilon_l} \right),$$

where  $v_{ph}$  – the phase velocity;  $k_B$  – the Boltzmann constant.

It is known that in thin films or small particles we observe a decrease  $\Theta_D$  (see, for example, [1]), which increases the mean square displacement of atoms as  $\overline{u^2} \cong \left( \frac{T}{\Theta_D} \right)^2$ . Increase  $\overline{u^2}$  determines some effective

increase  $\mu_f' = -\frac{d \ln d}{d \ln l}$ . Qualitative considerations indicate that the longitudinal deformation film value  $\Theta_D$  will also generally decrease, although strain causes a slight increase. Thus, in all film materials value  $\mu_f$  must be somewhat overpriced compared to bulk samples.

Another mechanism an increase  $\mu_f'$  is associated with in some reduction in thickness  $\Delta d'$  due to diffusion of surface atoms at grain boundaries, which during deformation  $\Delta \varepsilon_{l,t} > 0$  width will increase. The smoothing relief of film surface will cause an additional contribution  $\Delta \mu_f'$  in value  $\mu_f'$ .

And, finally, may also result in a decrease  $\gamma$  of the reduction  $(2\gamma - 4\mu_f\gamma)$  plugin that causes a change  $\gamma_l$  downward.

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